

isc Silicon NPN Power Transistor

FJA4313

DESCRIPTION

- · High Collector Breakdown Voltage-
- : V_{(BR)CEO}= 230V(Min.)
- Good Linearity of h_{FE}
- Complement to Type FJA4213
- Minimum Lot-to-Lot variations for robust device performant and reliable operation

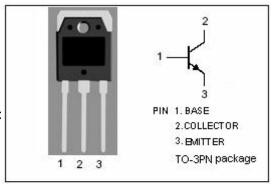


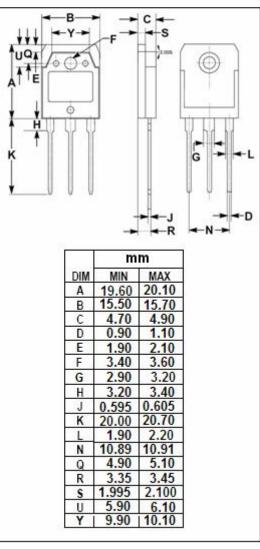
APPLICATIONS

- · Power amplifier applications
- Recommend for 80W high fidelity audio frequency amplifier output stage applications



| SYMBOL | PARAMETER | VALUE | UNIT |
|------------------|--|-------|------------|
| V _{CBO} | Collector-Base Voltage | 230 | V |
| V _{CEO} | Collector-Emitter Voltage | 230 | V |
| V _{EBO} | Emitter-Base Voltage | 5 | V |
| lc | Collector Current-Continuous | 15 | Α |
| I _B | Base Current-Continuous | 1.5 | Α |
| Pc | Collector Power Dissipation @ T _C =25℃ | | W |
| TJ | Junction Temperature | 150 | $^{\circ}$ |
| T _{stg} | Storage Temperature Range -55~150 | | $^{\circ}$ |







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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

| SYMBOL | PARAMETER | CONDITIONS | MIN | TYP. | MAX | UNIT |
|-----------------------|--------------------------------------|---|-----|------|-----|------------|
| V _(BR) CEO | Collector-Emitter Breakdown Voltage | I _C = 10mA ; R _{BE} = ∞ | 230 | | | V |
| V _{(BR)CBO} | Collector-Base Breakdown Voltage | I _C = 5mA; I _E = 0 | 230 | | | V |
| V _{(BR)EBO} | Emitter-Base Breakdown Voltage | I _E = 5mA; I _C = 0 | 5 | | | V |
| V _{CE} (sat) | Collector-Emitter Saturation Voltage | I _C = 8A; I _B = 0.8A | | | 3.0 | V |
| $V_{BE(on)}$ | Base-Emitter On Voltage | I _C = 7A; V _{CE} = 5V | | | 1.5 | V |
| I _{CBO} | Collector Cutoff Current | V _{CB} = 230V ; I _E = 0 | | | 5 | μ A |
| І ЕВО | Emitter Cutoff Current | V _{EB} = 5V; I _C = 0 | | | 5 | μ А |
| h _{FE-1} | DC Current Gain | I _C = 1A; V _{CE} = 5V | 55 | | 160 | |
| h _{FE-2} | DC Current Gain | I _C = 7A; V _{CE} = 5V | 35 | | | |
| Сов | Output Capacitance | I _E = 0; V _{CB} = 10V; f _{test} = 1.0MHz | | 200 | | pF |
| f⊤ | Current-Gain—Bandwidth Product | I _C = 1A; V _{CE} = 5V | | 30 | | MHz |

♦ h_{FE-1} Classifications

| R | 0 | | |
|--------|--------|--|--|
| 55-110 | 80-160 | | |



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